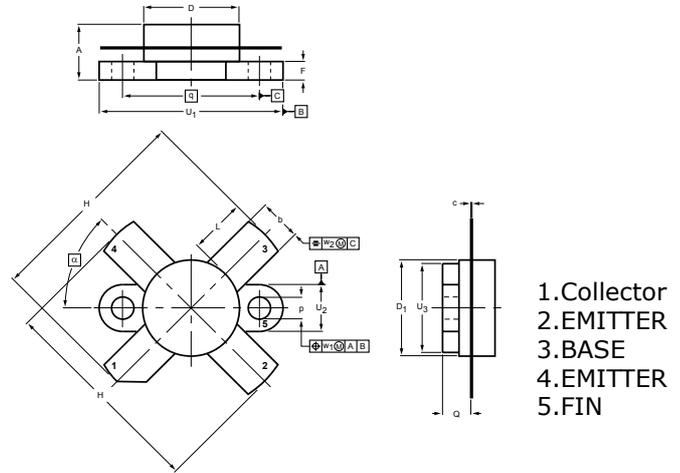


DESCRIPTION

Designed primarily for 2-30MHz SSB linear power amplifier applications (low supply voltage use)

FEATURES

- Specified 12.5V, 28MHz Characteristics
- $P_o = 100W$ PEP
- $G_p = 15.2$ Typ. at 100 W/28 MHz
- IMD3 = -24 dBc max. at 100 W(PEP)
- Omnigold™ Metalization System



DIMENSIONS

NOTE: ALL ELECTRODES ARE ISOLATED FROM FLANGE.

UNIT	A	b	c	D	D ₁	F	H	L	p	Q	q	U ₁	U ₂	U ₃	w ₁	w ₂	α
mm	7.27 6.17	5.82 5.56	0.16 0.10	12.86 12.59	12.83 12.57	2.67 2.41	28.45 25.52	7.93 6.32	3.30 3.05	4.45 3.91	18.42	24.90 24.63	6.48 6.22	12.32 12.06	0.51	1.02	45°
inches	0.286 0.243	0.229 0.219	0.006 0.004	0.506 0.496	0.505 0.495	0.105 0.095	1.120 1.005	0.312 0.249	0.130 0.120	0.175 0.154	0.725	0.98 0.97	0.255 0.245	0.485 0.475	0.02	0.04	

MAXIMUM RATINGS

CHARACTERISTICS	SYMBOL	RATINGS	UNITS
Collector-Base Voltage	V _{CB0}	45	V
Collector-Emitter Voltage	V _{CES}	45	V
Collector-Emitter Voltage	V _{CEO}	18	V
Collector Current	I _C	25	A
Emitter-Base Voltage	V _{EBO}	4	V
Collector Power Dissipation	P _{DISS}	250	W
Junction Temperature	T _J	175	°C
Storage Temperature Range	T _{STG}	-65 to 175	°C

ELECTRICAL CHARACTERISTICS

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	I _C =100mA, I _B =0	18	-	-	V
Collector-Emitter Breakdown Voltage	V _{(BR)CES}	I _C =100mA, V _{EB} =0	45	-	-	V
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	I _E =1mA, I _C =0	4	-	-	V
DC Current Gain	h _{FE}	V _{CE} =5V, I _C =10A	10	-	150	
Collector Output Capacitance	C _{ob}	V _{CB} =12.5V, I _E =0 f=1MHz	-	700	-	pF
Power Gain	G _p	V _{CC} =12.5V, P _{OUT} =100W I _{idle} =100mA, f=28MHz	13.0	15.2	-	dB
Collector Efficiency	η _c		35	-	-	%
Intermodulation Distortion	IMD3		-	-	-24	dBc
Series Equivalent Input Impedance	Z _{IN}	V _{CC} =12.5V P _{OUT} =100W	-	1.45 - j0.95	-	Ω
Series Equivalent Output Impedance	Z _{OUT}	f=28MHz	-	1.45 - j1.0	-	Ω

Note : Above parameters , ratings , limits and conditions are subject to change.